

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07354 DT-33-21

**2SB754**

SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

Unit in mm

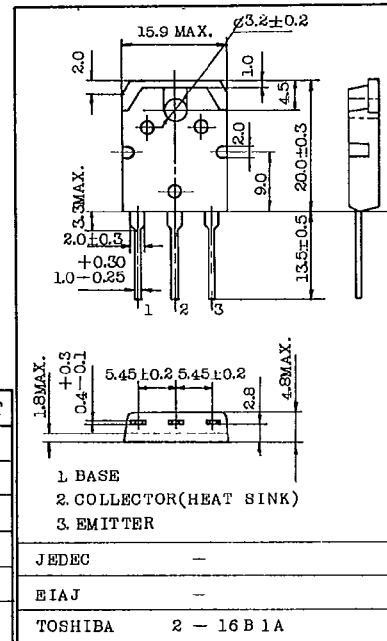
HIGH CURRENT SWITCHING APPLICATIONS.  
POWER AMPLIFIER APPLICATIONS.

## FEATURES:

- High Collector Current :  $I_C = -7A$
- Low Collector Saturation Voltage  
:  $V_{CE(sat)} = -0.4V$  (Max.) at  $I_C = -4A$
- High Power Dissipation :  $P_C = 60W$  at  $T_c = 25^\circ C$
- Complementary to 2SD844.

## MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-7	A
Emitter Current	$I_E$	7	A
Collector Power Dissipation	$P_C$	Ta=25°C	2.5
		Tc=25°C	60
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C



Weight : 4.6g

## ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = -50V, I_E = 0$	-	-	-10	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$	-	-	-10	$\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -50mA, I_B = 0$	-50	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -10mA, I_C = 0$	-5	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -1V, I_C = -1A$	70	-	240	
	$h_{FE(2)}$	$V_{CE} = -1V, I_C = -4A$	30	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -4A, I_B = -0.4A$	-	-0.2	-0.4	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = -1V, I_C = -4A$	-	-0.9	-1.2	V
Transition Frequency	$f_T$	$V_{CE} = -5V, I_C = -1A$	-	10	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	300	-	pF

Note :  $h_{FE(1)}$  Classification O : 70~140 Y : 120~240

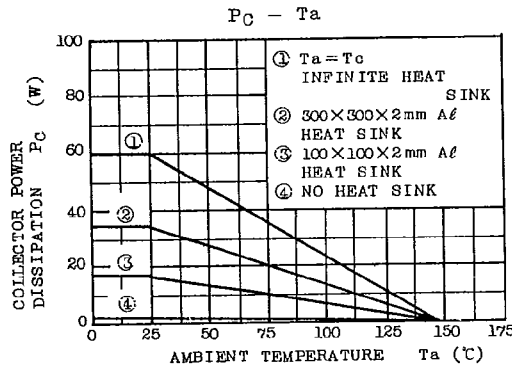
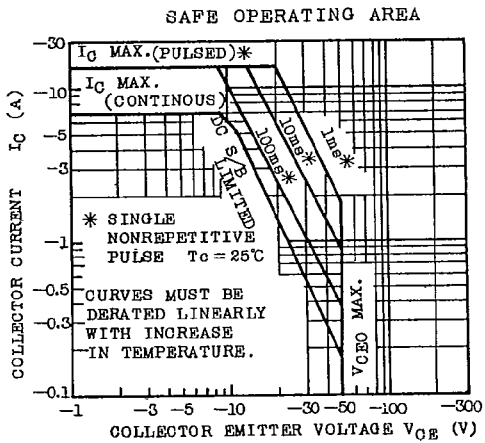
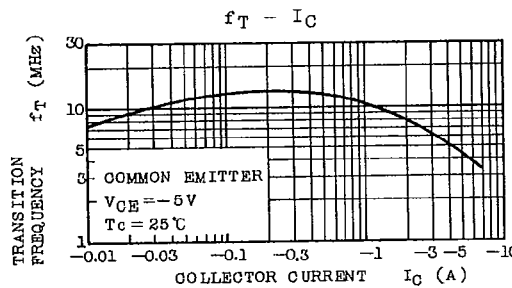
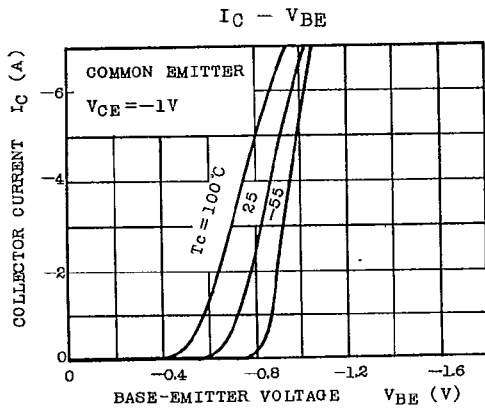
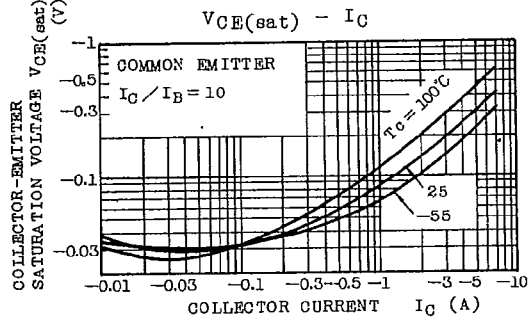
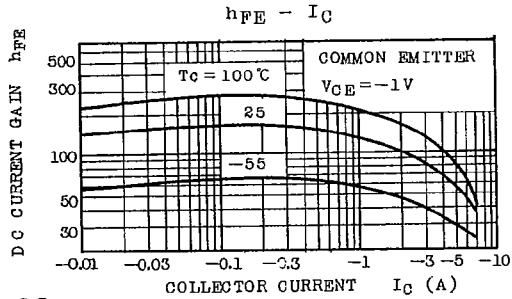
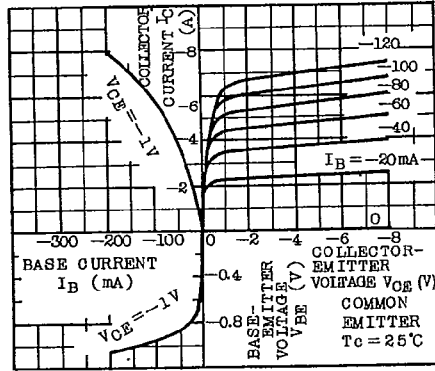
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STATIC CHARACTERISTICS



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